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Kind regards,

Team Nexperia

# 74HC1G32-Q100; 74HCT1G32-Q100

## 2-input OR gate

Rev. 1 — 8 August 2012

Product data sheet

### 1. General description

74HC1G32-Q100 and 74HCT1G32-Q100 are high-speed Si-gate CMOS devices. They provide a 2-input OR function.

The standard output currents are half of those of the 74HC32-Q100 and 74HCT32-Q100.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

### 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$
- Input levels:
  - ◆ For 74HC1G32-Q100: CMOS level
  - ◆ For 74HCT1G32-Q100: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
  - ◆ MIL-STD-883, method 3015 exceeds 2000 V
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V ( $C = 200\text{ pF}$ ,  $R = 0\text{ }\Omega$ )
- SOT353-1 and SOT753 package options

### 3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74HC1G32GW-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74HCT1G32GW-Q100				
74HC1G32GV-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74HCT1G32GV-Q100				



## 4. Marking

Table 2. Marking codes

Type number	Marking code <sup>[1]</sup>
74HC1G32GW-Q100	HG
74HCT1G32GW-Q100	TG
74HC1G32GV-Q100	H32
74HCT1G32GV-Q100	T32

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 5. Functional diagram

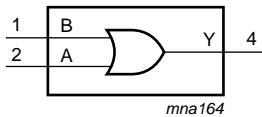


Fig 1. Logic symbol

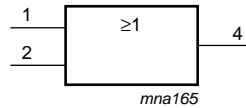


Fig 2. IEC logic symbol

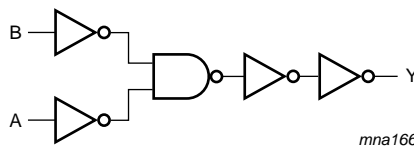


Fig 3. Logic diagram

## 6. Pinning information

### 6.1 Pinning

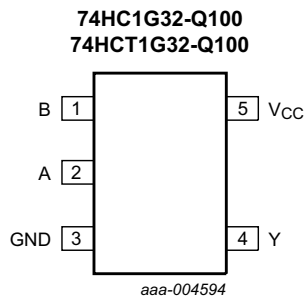


Fig 4. Pin configuration

## 6.2 Pin description

**Table 3.** Pin description

Symbol	Pin	Description
B	1	data input B
A	2	data input A
GND	3	ground (0 V)
Y	4	data output Y
V <sub>CC</sub>	5	supply voltage

## 7. Functional description

**Table 4.** Function table

H = HIGH voltage level; L = LOW voltage level

Inputs		Output
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	H

## 8. Limiting values

**Table 5.** Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [\[1\]](#)

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V or V <sub>I</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < -0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>O</sub>	output current	-0.5 V < V <sub>O</sub> < V <sub>CC</sub> + 0.5 V	-	±12.5	mA
I <sub>CC</sub>	supply current		-	25	mA
I <sub>GND</sub>	ground current		-25	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	<a href="#">[2]</a> -	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G32-Q100			74HCT1G32-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 2.0 V	-	-	625	-	-	-	ns/V
		V <sub>CC</sub> = 4.5 V	-	-	139	-	-	139	ns/V
		V <sub>CC</sub> = 6.0 V	-	-	83	-	-	-	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T<sub>amb</sub> = 25 °C.

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
<b>74HC1G32-Q100</b>								
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	V
		V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 6.0 V	5.9	6.0	-	5.9	-	V
		I <sub>O</sub> = -2.0 mA; V <sub>CC</sub> = 4.5 V	4.13	4.32	-	3.7	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 2.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.33	-	0.4	V
		I <sub>O</sub> = 2.6 mA; V <sub>CC</sub> = 6.0 V	-	0.16	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	1.0	-	1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	10	-	20	μA
C <sub>I</sub>	input capacitance		-	1.5	-	-	-	pF

**Table 7. Static characteristics ...continued**

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
<b>74HCT1G32-Q100</b>								
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	2.0	1.6	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	1.2	0.8	-	0.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5\text{ V}$						
		$I_O = -20\text{ }\mu\text{A}$	4.4	4.5	-	4.4	-	V
		$I_O = -2.0\text{ mA}$	4.13	4.32	-	3.7	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5\text{ V}$						
		$I_O = 20\text{ }\mu\text{A}$	-	0	0.1	-	0.1	V
		$I_O = 2.0\text{ mA}$	-	0.15	0.33	-	0.4	V
$I_I$	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5\text{ V}$	-	-	1.0	-	1.0	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$ ; $V_{CC} = 5.5\text{ V}$	-	-	10	-	20	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	per input; $V_{CC} = 4.5\text{ V to }5.5\text{ V}$ ; $V_I = V_{CC} - 2.1\text{ V}$ ; $I_O = 0\text{ A}$	-	-	500	-	850	$\mu\text{A}$
$C_I$	input capacitance		-	1.5	-	-	-	pF

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**

$GND = 0\text{ V}$ ;  $t_r = t_f \leq 6.0\text{ ns}$ . All typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ . For test circuit see [Figure 6](#)

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
<b>74HC1G32-Q100</b>								
$t_{pd}$	propagation delay	A and B to Y; see <a href="#">Figure 5</a>						
		$V_{CC} = 2.0\text{ V}$ ; $C_L = 50\text{ pF}$	-	18	115	-	135	ns
		$V_{CC} = 4.5\text{ V}$ ; $C_L = 50\text{ pF}$	-	8	23	-	27	ns
		$V_{CC} = 5.0\text{ V}$ ; $C_L = 15\text{ pF}$	-	8	-	-	-	ns
		$V_{CC} = 6.0\text{ V}$ ; $C_L = 50\text{ pF}$	-	7	20	-	23	ns
$C_{PD}$	power dissipation capacitance	$V_I = GND$ to $V_{CC}$	-	19	-	-	-	pF

**Table 8. Dynamic characteristics ...continued**

$GND = 0\text{ V}$ ;  $t_r = t_f \leq 6.0\text{ ns}$ . All typical values are measured at  $T_{amb} = 25\text{ }^\circ\text{C}$ . For test circuit see [Figure 6](#)

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
<b>74HCT1G32-Q100</b>								
$t_{pd}$	propagation delay	A and B to Y; see <a href="#">Figure 5</a>	<a href="#">[1]</a>					
		$V_{CC} = 4.5\text{ V}$ ; $C_L = 50\text{ pF}$	-	10	24	-	27	ns
		$V_{CC} = 5.0\text{ V}$ ; $C_L = 15\text{ pF}$	-	10	-	-	-	ns
$C_{PD}$	power dissipation capacitance	$V_I = GND\text{ to }V_{CC} - 1.5\text{ V}$	<a href="#">[2]</a>					

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2]  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu\text{W}$ ).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

$f_i$  = input frequency in MHz

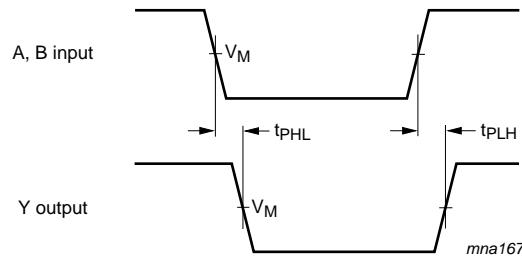
$f_o$  = output frequency in MHz

$C_L$  = output load capacitance in pF

$V_{CC}$  = supply voltage in V

$\sum (C_L \times V_{CC}^2 \times f_o)$  = sum of outputs

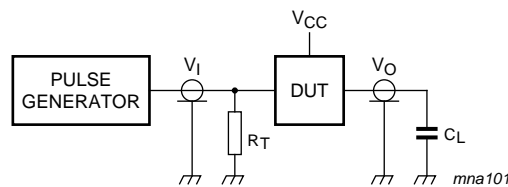
## 12. Waveforms



For 74HC1G32-Q100:  $V_M = 0.5 \times V_{CC}$ ;  $V_I = GND\text{ to }V_{CC}$

For 74HCT1G32-Q100:  $V_M = 1.3\text{ V}$ ;  $V_I = GND\text{ to }3.0\text{ V}$

**Fig 5. The input (A and B) to output (Y) propagation delays**



Measurement points are given in [Table 8](#). Definitions for test circuit:

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

**Fig 6. Load circuitry for switching times**

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

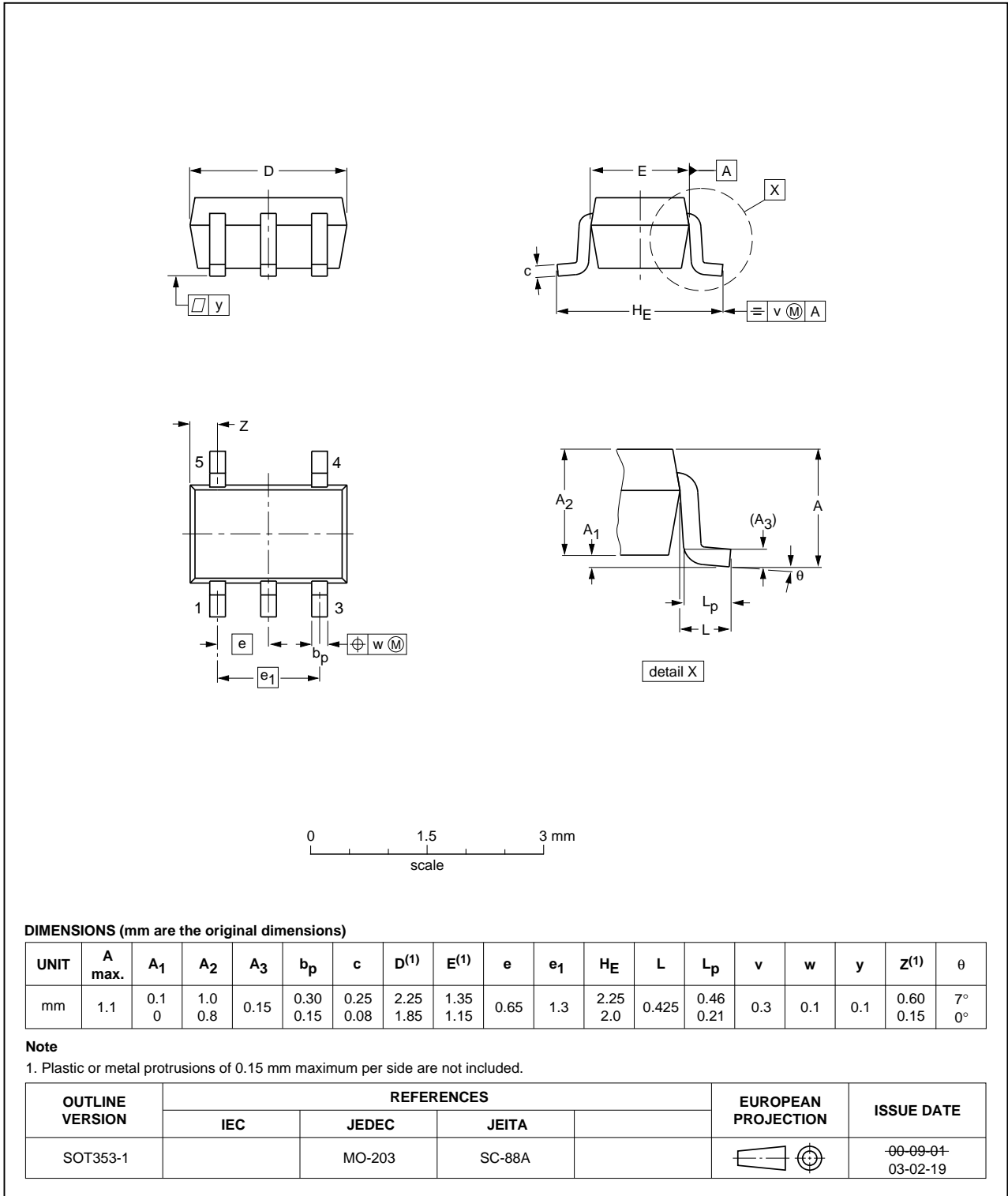


Fig 7. Package outline SOT353-1 (TSSOP5)



Plastic surface-mounted package; 5 leads

SOT753

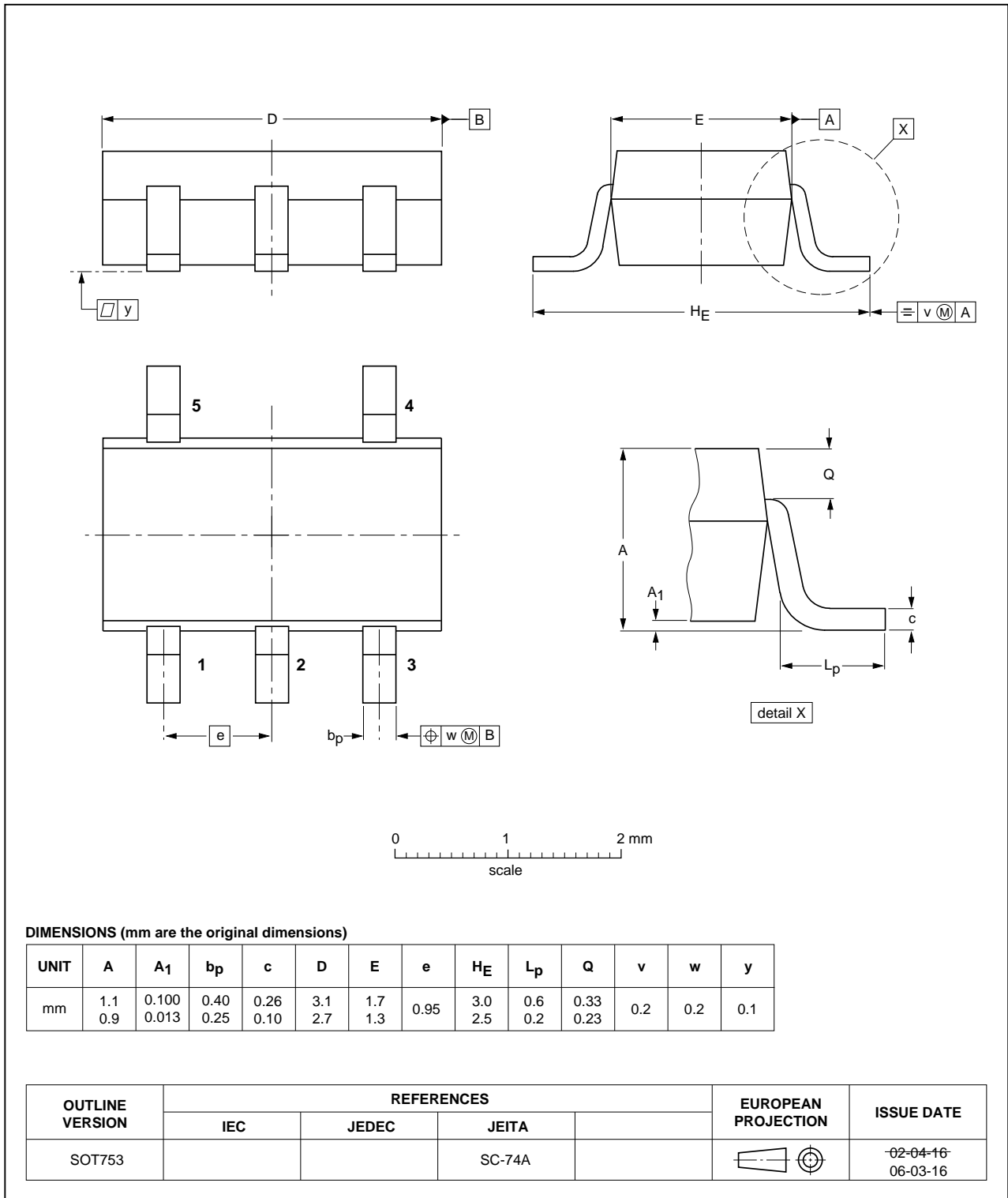


Fig 8. Package outline SOT753 (SC-74A)

## 14. Abbreviations

Table 9. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test
MIL	Military

## 15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G32_Q100 v.1	20120808	Product data sheet	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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